

SUSCEPTOR DESIGNS FOR SILICON CARBIDE THIN FILMS

Abstract of the Disclosure

A susceptor is disclosed for minimizing or eliminating thermal gradients that affect a substrate wafer during epitaxial growth. The susceptor comprises a first susceptor portion including a surface for receiving a semiconductor substrate wafer thereon, and a second susceptor portion facing the substrate-receiving surface and spaced from the substrate-receiving surface. The spacing is sufficiently large to permit the flow of gases therebetween for epitaxial growth on a substrate on the surface, while small enough for the second susceptor portion to heat the exposed face of a substrate to substantially the same temperature as the first susceptor portion heats the face of a substrate that is in direct contact with the substrate-receiving surface.

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